

# Specification Sheet

P Type Silicon Wafers

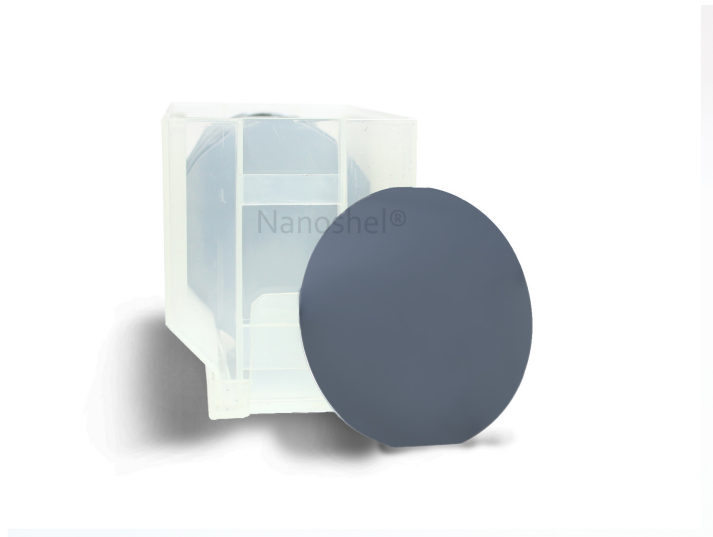
(4 inch, Boron Doping)

Stock No: NS6130-10-1199, CAS: 7440-21-3

<b>Product</b>	:	<b>Silicon Wafer 4"</b>
Stock No	:	NS6130-10-1199
CAS	:	7440-21-3
Diameter	:	4"
Thickness	:	525 ± 25µm
Dopant	:	Boron
Crystal Orientation	:	< 100>
Type	:	P
Growth Method	:	CZ
Resistivity	:	1.0-5.0Ω.cm
TTV	:	< 10.0µm
STIR	:	< 2µm
GLOBAL TIR	:	< 5µm
Warp	:	< 50.0µm
LPD	:	< 30 counts @ particles size>0.3µm
Laser Mark	:	None
Edge Profile	:	Rounded
Front Surface	:	Polished
Back Surface	:	Etched
Bow	:	< 50.0µm
<b>Main Inspect Verifier</b>	:	<b>Manager QC</b>

**Note:** Product Specification are subject to amendment and may change over time

## Characterization of P Type Silicon Wafers



P Type Silicon Wafers



**NANOSHEL**  
Creating Miracles in Black